

Features

- Uses CRM(CQ) advanced Trench technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Applications

- Motor control and drive
- Battery management
- UPS (Uninterruptible Power Supplies)

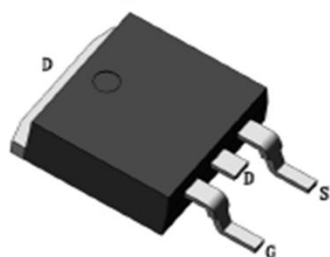
Product Summary

V_{DS}	100V
$R_{DS(on)}$ typ.	6.2mΩ
I_D	130A

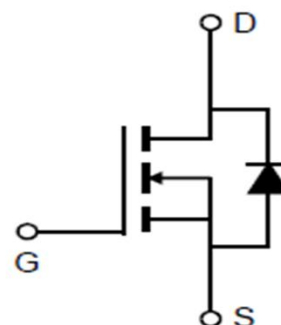
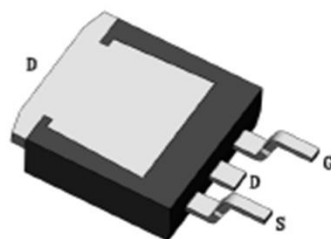
100% DVDS Tested
100% Avalanche Tested

TO-263

Top View



Bottom View


Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRTS095N10NZ	CRTS095N10NZ	TO-263	Reel	N/A	N/A	800pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	100	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit) $T_C = 25^\circ\text{C}$ (Package limit) $T_C = 100^\circ\text{C}$ (Silicon limit)	I_D	130 160 82	A
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	$I_{D\ pulse}$	520	A
Avalanche energy, single pulse ($L=0.5\text{mH}$, $R_g=25\Omega$)	E_{AS}	400	mJ
Gate-Source voltage	V_{GS}	± 25	V
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	280	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ\text{C}$
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Typ	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.34	0.45	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}^*	65	91	

Electrical Characteristic (at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	100	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	2.4	3	3.6	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	0.05	1	μA	$V_{DS}=100V, V_{GS}=0V$ $T_j=25^\circ C$ $T_j=150^\circ C$
Gate-source leakage current	I_{GSS}	-	± 10	± 100	nA	$V_{GS}=\pm 25V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	6.2	9.5	mΩ	$V_{GS}=10V, I_D=50A,$ $T_j=25^\circ C$ $T_j=150^\circ C$
Transconductance	g_{fs}	-	110	-	S	$V_{DS}=5V, I_D=50A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	7431	13376	pF	$V_{GS}=0V, V_{DS}=50V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	617	1111		
Reverse Transfer Capacitance	C_{rss}	-	254	508		
Gate Total Charge	Q_G	-	168	269	nC	$V_{GS}=10V, V_{DS}=50V,$ $I_D=50A, f=1MHz$
Gate-Source charge	Q_{gs}	-	43	69		
Gate-Drain charge	Q_{gd}	-	52	83		
Turn-on delay time	$t_{d(on)}$	-	27	-	ns	$V_{GS}=10V, V_{DD}=50V,$ $R_{G_ext}=2.7\Omega, I_D=50A$
Rise time	t_r	-	97	-		
Turn-off delay time	$t_{d(off)}$	-	84	-		
Fall time	t_f	-	102	-		
Gate resistance	R_G	-	1.2	3	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.9	1.3	V	$V_{GS}=0V, I_{SD}=50A$
Body Diode Continuous Forward Current	I_S			130	A	$T_C = 25^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	85	128	ns	$I_F=50A, dI/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	-	263	395	nC	

*The value of R_{thJA} is measured by placing the device in a still air box which is one cubic foot.

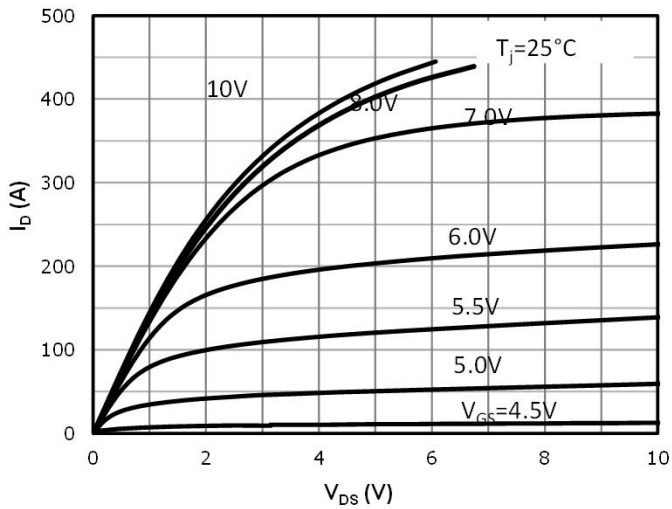
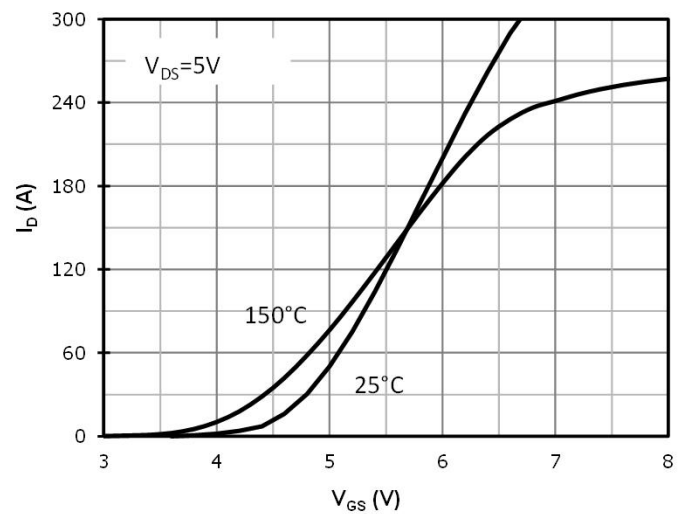
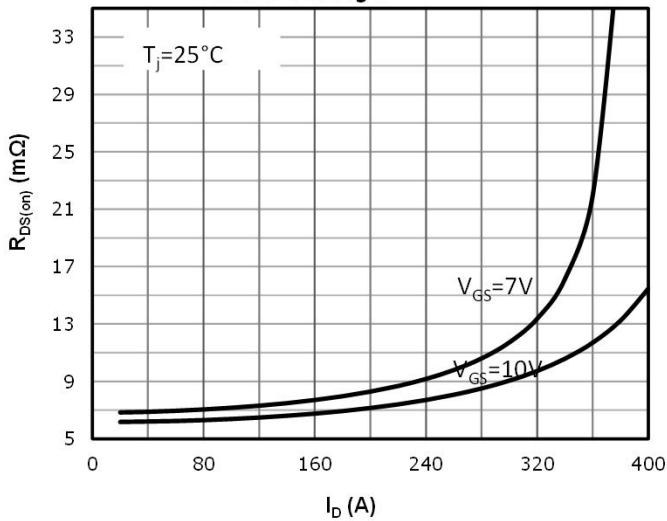
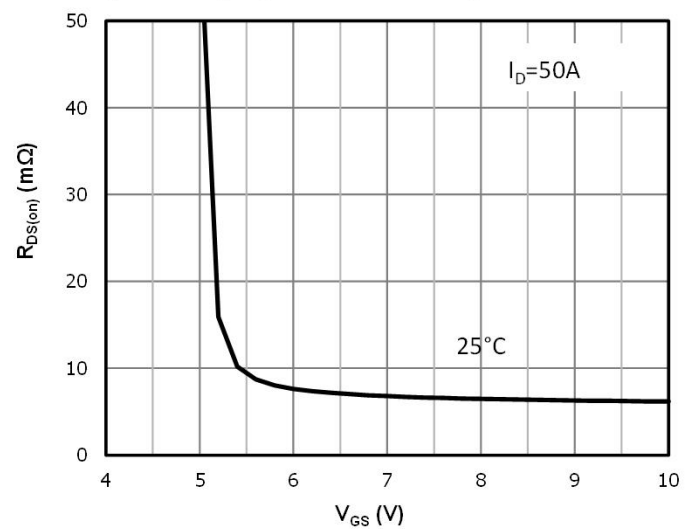
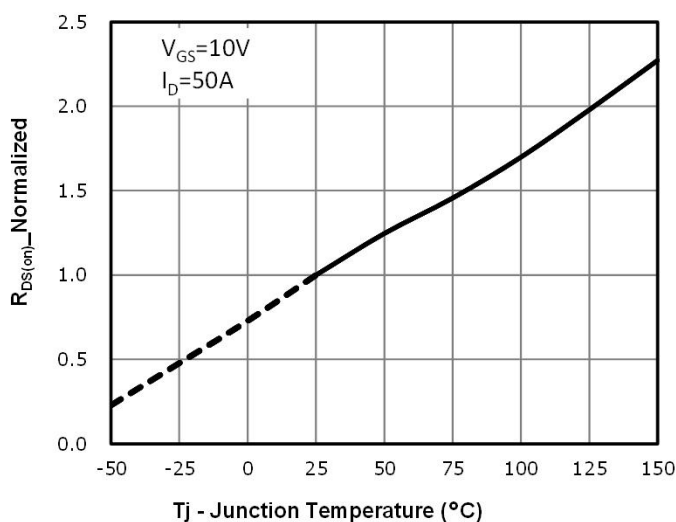
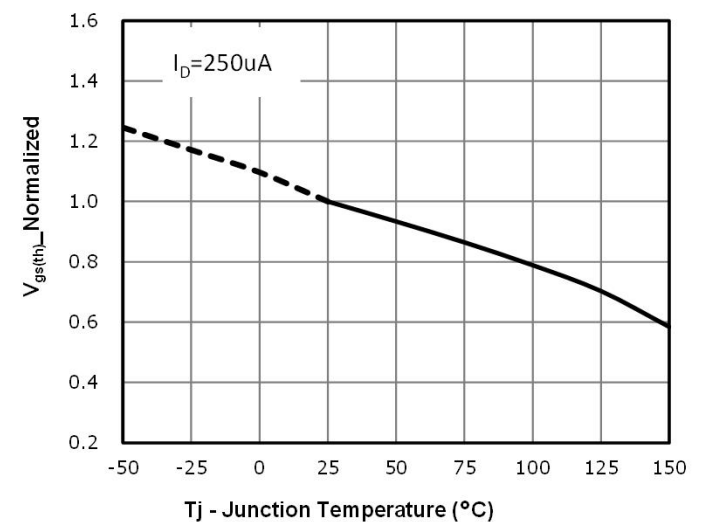
Typical Performance Characteristics
Fig 1: Output Characteristics

Fig 2: Transfer Characteristics

Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

Fig 4: $R_{DS(on)}$ vs Gate Voltage

Fig 5: $R_{DS(on)}$ vs. Temperature

Fig 6: $V_{GS(th)}$ vs. Temperature


Fig 7: Gate Charge Characteristics

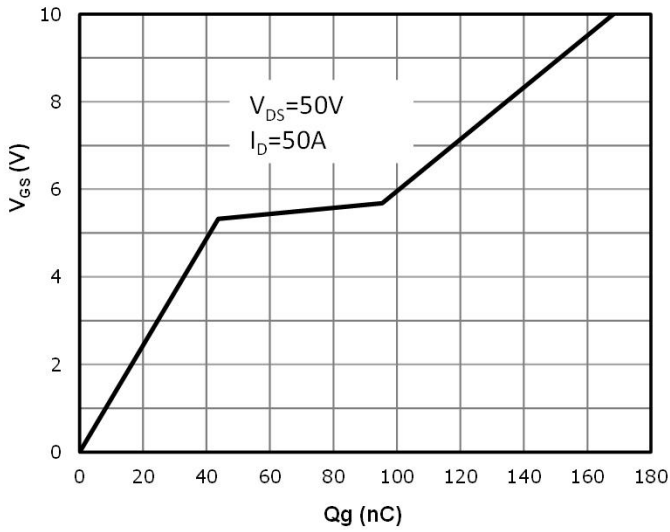


Fig 8: Capacitance Characteristics

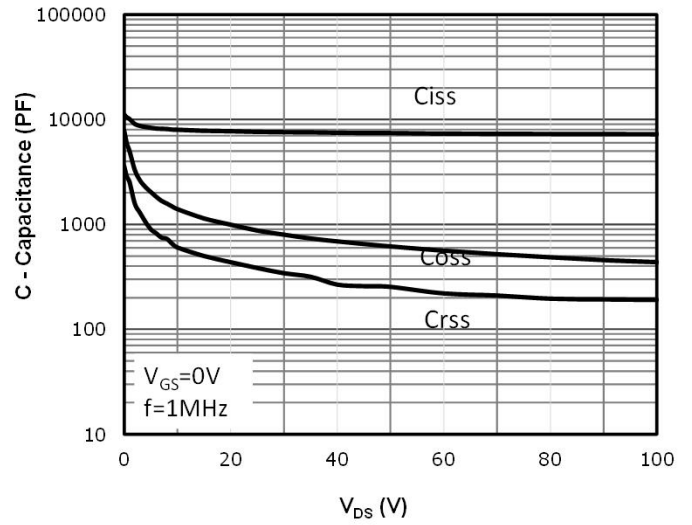


Fig 9: Body-diode Forward Characteristics

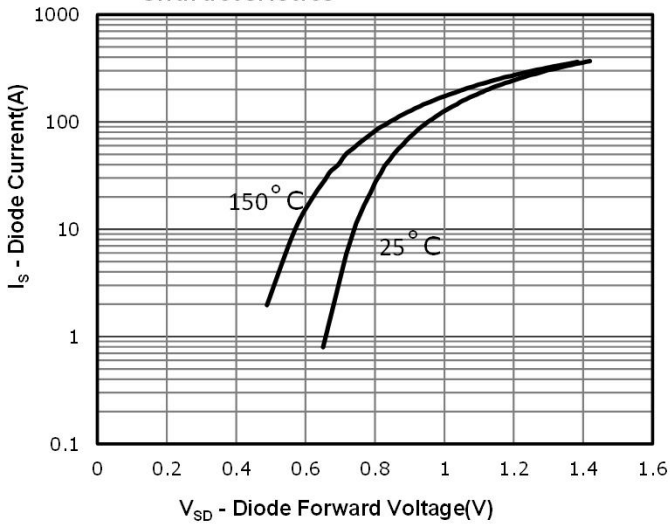


Fig 10: Power Dissipation

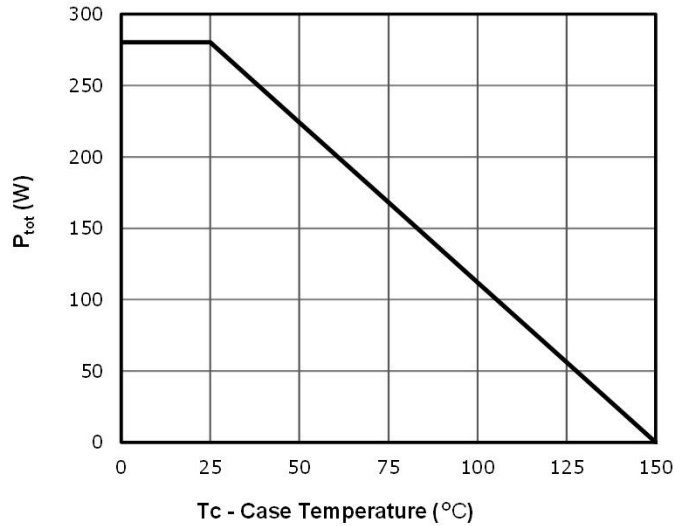


Fig 11: Drain Current Derating

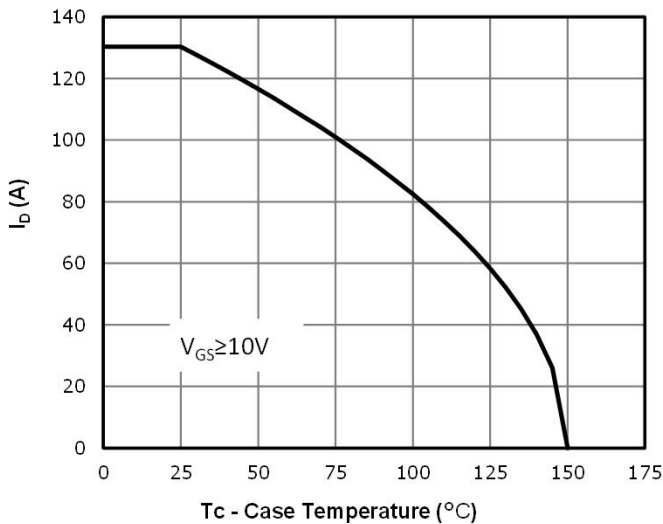


Fig 12: Safe Operating Area

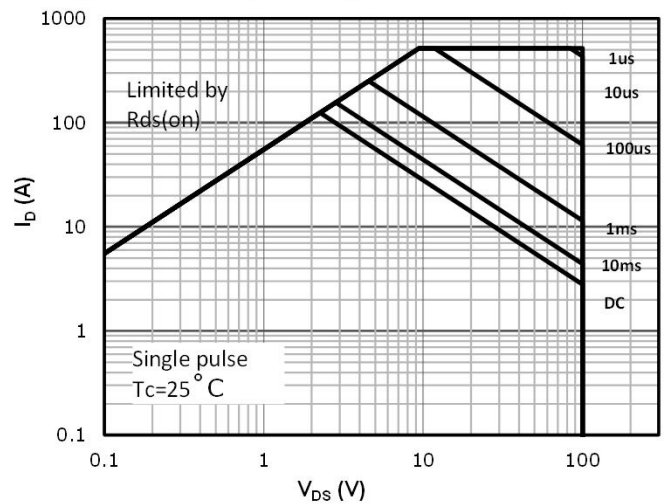
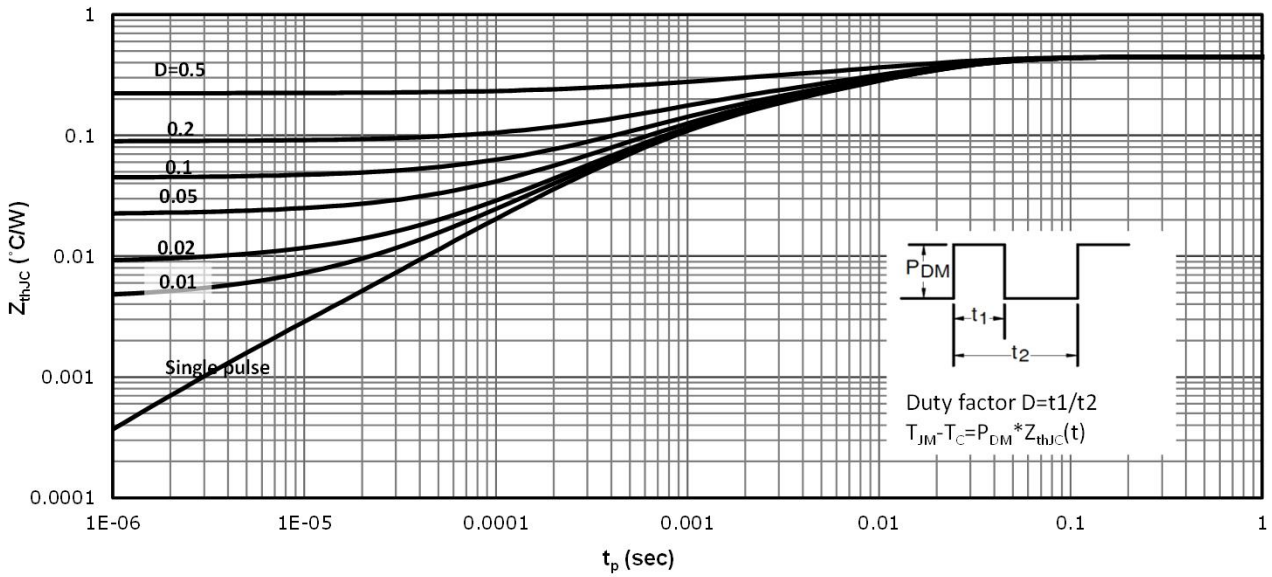
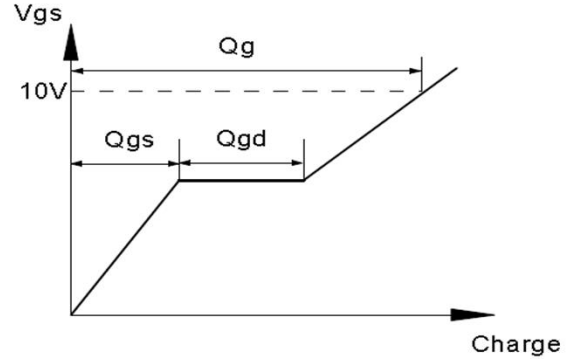
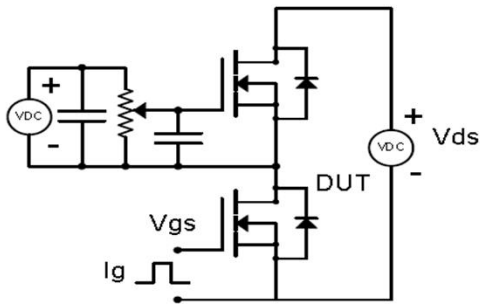


Fig 13: Max. Transient Thermal Impedance

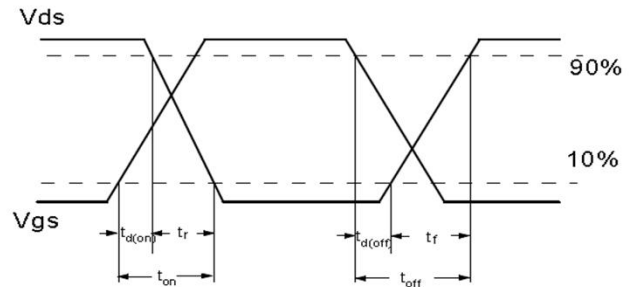
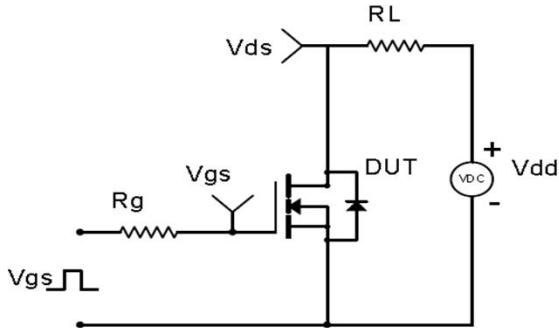


Test Circuit & Waveform

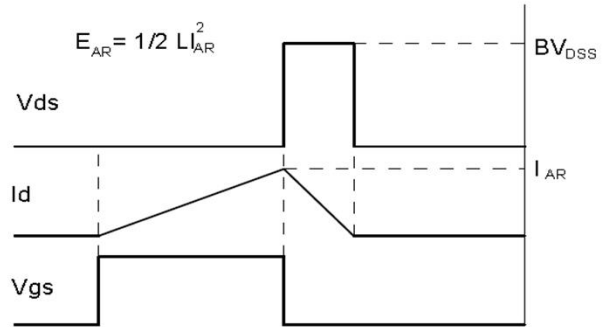
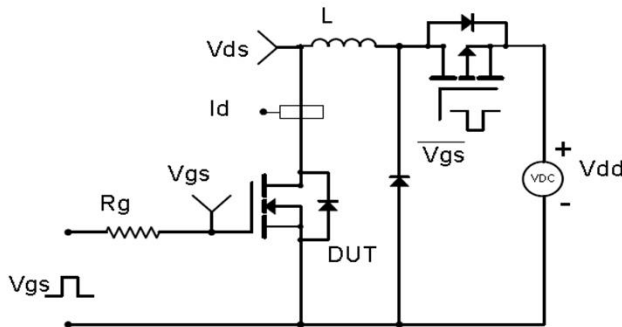
Gate Charge Test Circuit & Waveform



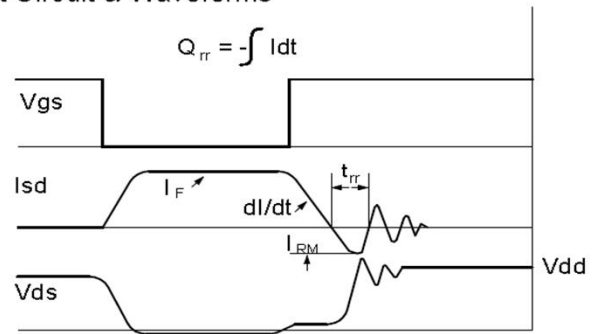
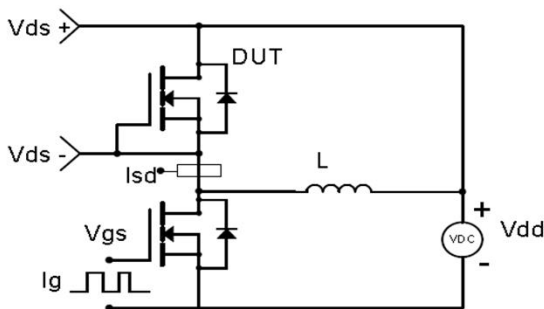
Resistive Switching Test Circuit & Waveforms

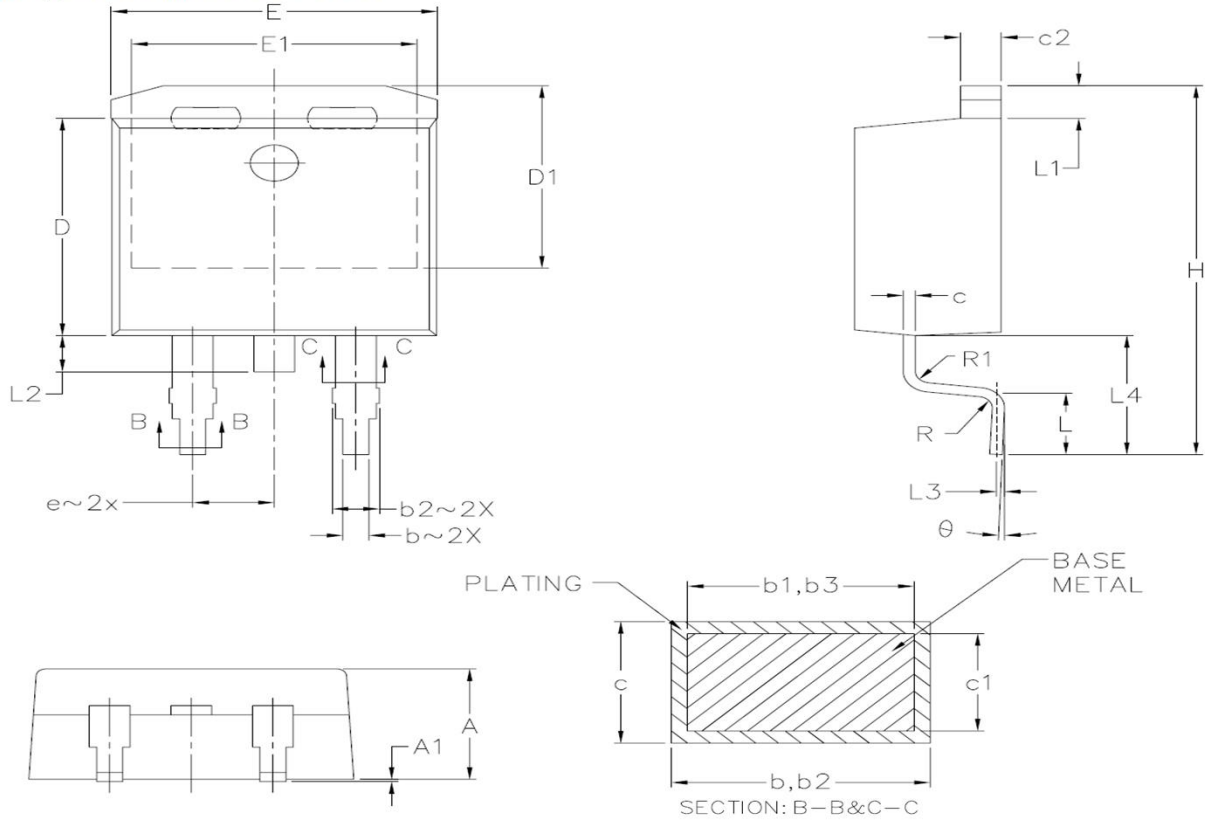


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



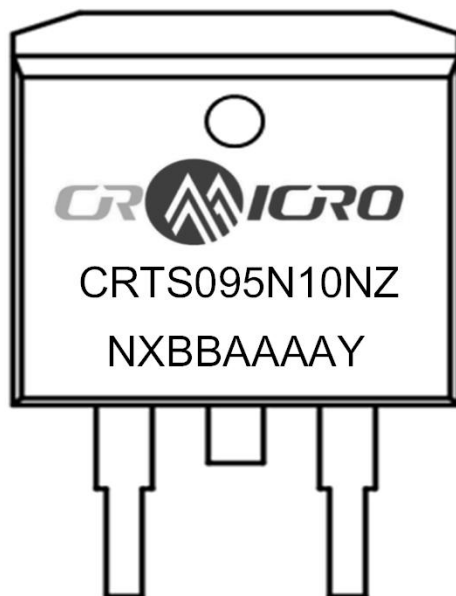
Diode Recovery Test Circuit & Waveforms



Package Outline: TO-263


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.060	4.830	0.160	0.190
A1	0.000	0.254	0.000	0.010
b	0.500	0.991	0.020	0.039
b1	0.500	0.890	0.020	0.035
b2	1.140	1.780	0.045	0.070
b3	1.140	1.730	0.045	0.068
c	0.381	0.737	0.015	0.029
c1	0.381	0.584	0.015	0.023
c2	1.143	1.651	0.045	0.065
D	8.382	9.652	0.330	0.380
D1	6.858	--	0.270	--
e	2.54 BSC.		0.100 BSC.	
E	9.652	10.668	0.380	0.420
E1	6.223	--	0.245	--
H	14.605	15.880	0.575	0.625
L	1.778	2.794	0.070	0.110
L1	--	1.676	--	0.066
L2	--	1.778	--	0.070
L3	0.254 BSC.		0.010 BSC.	
L4	4.780	5.280	0.188	0.208
θ	0°	8°	0°	8°

Marking



NOTE:

NXBBAAAAY

- N —Wire Bond code
- X —Assembly location code
- BB —Fab code
- AAAA —Lot code
- Y —Bin code

Revision History

Revision	Date	Major changes
1.0	2022/9/1	Release of formal version

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

单击下面可查看定价，库存，交付和生命周期等信息

[>>CRMICRO\(华润微\)](#)